

HFA35HB60 PD-20379E

Ultrafast, Soft Recovery Diode Thru-Hole (TO-254AA) 600V, 22A

Features

- Single diode configuration
- Reduced RFI and EMI
- Reduced snubbing
- Extensive characterization of recovery parameters
- Hermetic package
- Ceramic eyelets

Product Summary

V_R: 600V

• **V**_F: 1.75V

Q_{rr}: 575nC

di_{(rec)M}/dt: 270A/μs

Potential Applications

- DC-DC converter
- Motor drives

Product Validation

Qualified according to MIL-PRF-19500 for space applications



Description

HFA35HB60 is part of the International Rectifier HiRel family of products. These diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems. An extensive characterization of the recovery behavior for different values of current, temperature and di/dt simplifies the calculations of losses in the operating conditions. The soft-ness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for power converters, motor drives and other applications where switching losses are significant portion of the total losses.

Ordering Information

Table 1 Ordering options

Part number	Package	Screening Level		
HFA35HB60	TO-254AA	сотѕ		
HFA35HB60SCV	TO-254AA	JANTXV-equivalent		
HFA35HB60SCX	TO-254AA	JANTX-equivalent		
HFA35HB60SCS	TO-254AA	S-level		

HFA35HB60

FRED Ultrafast, Soft Recovery Diode



Table of contents

Table of contents

Feat	tures	1
Pote	ential Applications	1
	duct Validation	
	cription	
	lering Information	
	ole of contents	
1		
- 2	Device Characteristics	
2.1		
2.2	Dynamic Recovery Characteristics	
2.3	Thermal-Mechanical Characteristics	4
3	Electrical Characteristics Curves	5
4	Test Circuit	8
5	Package Outline	
_	rision history	

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Absolute Maximum Ratings

1 Absolute Maximum Ratings

Table 2 Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
V_R	DC Reverse Voltage	600	V
I _F	Continuous Forward Current, T _C =100 °C ¹	22	А
I _{FSM}	Single pulse Forward Current, T _C = 25°C ²	225	А
P_{D} @ $T_{C} = 25^{\circ}C$	Maximum Power Dissipation	83	W
T _J T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C
Wt	Weight	9.3 (Typical)	g

¹ DC = 50% rect. wave

 $^{^2}$ ½ sine wave, 60 Hz, Pulse width = 8.33 ms



Device Characteristics

2 Device Characteristics

2.1 Electrical Characteristics

Table 3 Electrical Characteristics

Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Conditions
V_{BR}	Cathode Anode Breakdown Voltage	600	_	_	V	I _R = 100μA
V_{F}		_	_	1.55		I _F = 22A, T _J = -55°C
	Forward Voltage Drop See Fig. 1	_		1.75		$I_F = 22A, T_J = 25^{\circ}C$
		_	_	2.25	V	I _F = 45A, T _J = 25°C
		_	_	1.64		I _F = 22A, T _J = 125°C
I _R	Reverse Leakage Current	_	_	10	μΑ	$V_R = V_R$ Rated
	See Fig. 2	_	_	1.0	mA	V _R = 480V, T _J = 125°C
Ст	Junction Capacitance See Fig. 3	_	56	59	pF	V _R = 200V
Ls	Series Inductance	_	8.7	_	nH	Measured from center of bond pad to end of anode bonding wire

2.2 Dynamic Recovery Characteristics

Table 4 Dynamic Recovery Characteristics

Symbol	Parameter	Min.	Тур.	Мах.	Unit	Test Condition	S
t _{rr1}	Reverse Recovery Time	_	60	97		T _J = 25°C	
t _{rr2}	See Fig. 5	_	110	_	ns	T _J = 125°C	I _F = 22A
I _{RRM1}	Peak Recovery Current	_	5.2	_	_	T _J = 25°C	
I _{RRM2}	See Fig. 6	_	8.5	_	Α	T _J = 125°C	V _R = 200V
Q_{rr1}	Reverse Recovery Charge	_	190	575		T _J = 25°C	
Q _{rr2}	See Fig. 7	_	560	_	nC	T _J = 125°C	$d_{if}/dt = 200 A/ \mu s$
$di_{(rec)M}/dt_1$	Peak Rate of Fall of Recovery	_	270	_		T _J = 25°C	
di _{(rec)M} /dt ₂	Current During t₀ See Fig. 8	_	170	_	A/ μs	T _J = 125°C	

2.3 Thermal-Mechanical Characteristics

Table 5 Thermal-Mechanical Characteristics

Symbol	Parameter		Max.	Unit
$R_{ heta JC}$	Junction to Case, Single Leg Conducting		1.5	°C/W

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Electrical Characteristics Curves

3 Electrical Characteristics Curves

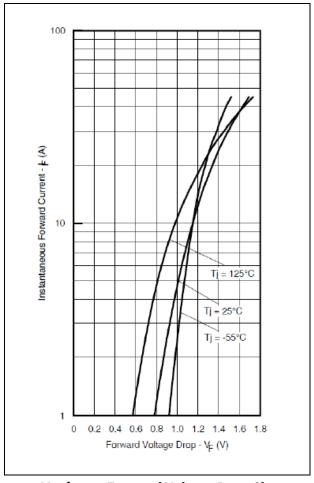


Figure 1 Maximum Forward Voltage Drop Characteristics

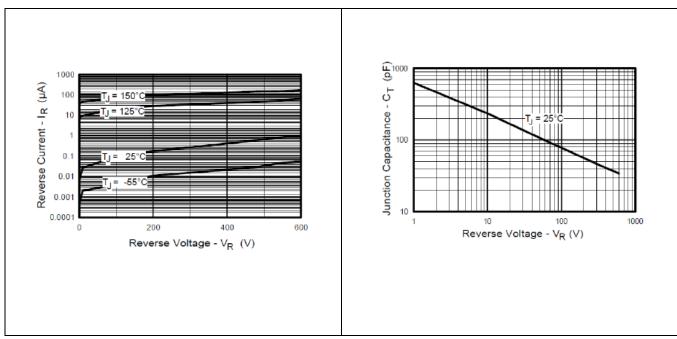


Figure 2 Typical Values of Reverse Current Vs. Reverse Voltage

Figure 3

Typical Junction Capacitance Vs. Reverse Voltage



Electrical Characteristics Curves

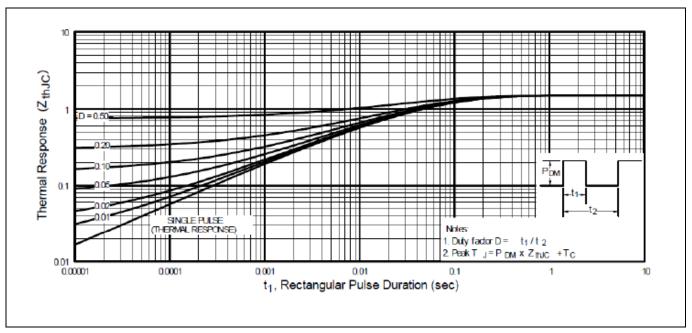


Figure 4 Maximum Thermal Impedance Z_{thJC} Characteristics

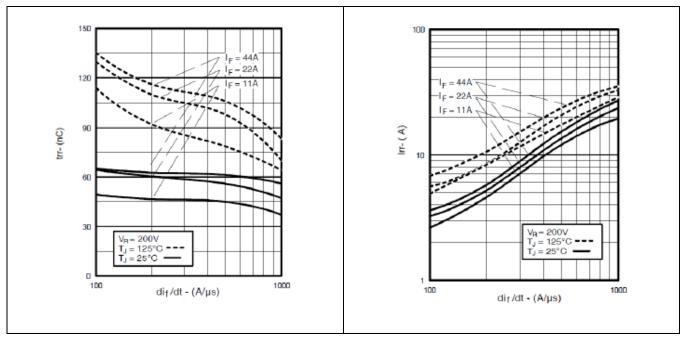


Figure 5 Typical Reverse Recovery Vs. d_{if}/dt Figure 6 Typical Recovery Current Vs. d_{if}/dt



Electrical Characteristics Curves

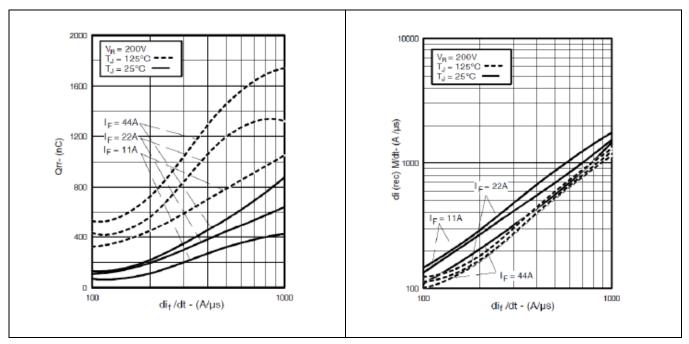


Figure 7 Typical Stored Charge Vs. d_{if}/dt

Figure 8 Typical di_{(rec)M}/dt Vs. d_{if}/dt



Test Circuit

4 Test Circuit

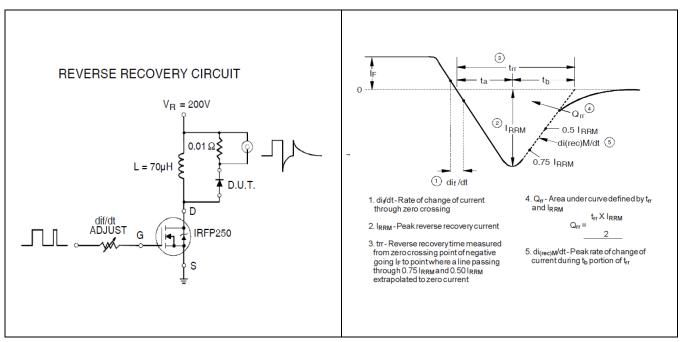


Figure 9 Reverse Recovery Parameter Test Circuit

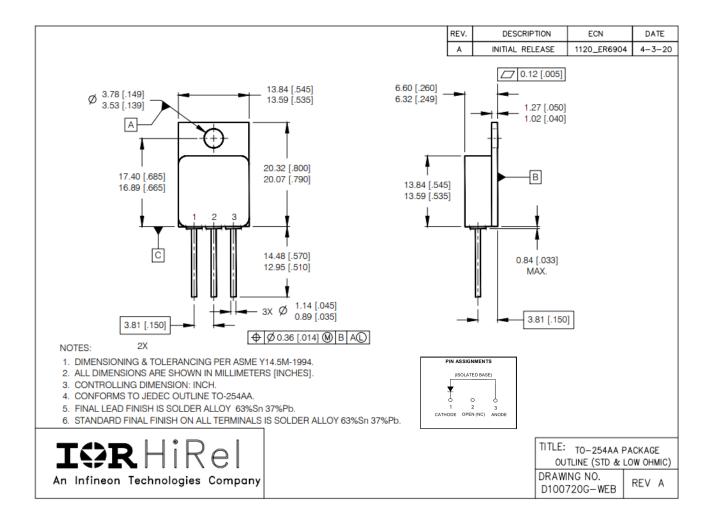
Figure 10 Reverse Recovery Waveform and Definitions



Package Outline

5 Package Outline

Note: For the most updated package outline, please see the website: TO-254AA



HFA35HB60

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Revision history

Revision history

Document version	Date of release	Description of changes
	12/24/2010	Final datasheet (PD-20379)
Rev A	03/07/2013	Updated per ECN-1120-00911
Rev B	09/23/2016	Updated per ECN-1120-04743
Rev C	03/02/2018	Updated per ECN-1120-06010
Rev D	05/03/2021	Updated per ECN-1120-08526
Rev E	06/02/2022	Updated per ECN-1120-08972

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